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The International Workshop on Computational Nanotechnology (IWCN) will be held from May 20-24, 2019, at the Hilton Orrington Evanston, Illinois, USA [1]. The abstract text should fit in one A4 page (210 mm x 297 mm, portrait, printable area 160 mm x 240 mm – top/bottom margins of 30 mm and left/right margins of 25 mm). An additional page is allowed for figures (see the second page of this template for the suggested format). Please underline the presenting author. Ensure that the e-mail address is correct, as it is used for further communications. Please do **not** insert any page number, header or footer. Please use Times New Roman font and do not forget to remove all ( )’s for instruction. Save your abstract as a **single Word DOCX** **file** with the file name, (presenter’s first name)\_(presenter’s family name).docx. For example, when the presenter is Akinobu Kanda, the file name is akinobu\_kanda.docx. If you submit more than one abstract as presenter, you may add a number at the end of the file name (e.g., akinobu\_kanda \_2.docx). Make sure that the DOCX file of your abstract is of camera-ready quality.

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[1] H. Tomori et al., Appl. Phys. Express, **4**, 075102 (2011).

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| Fig.1: The trap is connected to electrodes with the rates ΓN and Γ±. A magnetic field **B** defines the trap spin quantization axis OZ’ at an angle Θ to the magnetization orientation OZ in the ferromagnet. | Fig.4: Current as a function of Θ, for p=1, ΓN/ΓF = 10, ωL/ΓF = 1, ΓF T1 = 10, and several values of T2/T1. |
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| Fig.2: Current in units of eΓN as a function of Θ for p=1, ΓN/ΓF = 10, ωL/ΓF = 1, and several values of T2=T1. | Fig.5 Normalized current as a function of the position x relative to silicon, for p=1, ΓN=Γ0 exp(-x/d) , ΓF=Γ0 exp(-(d-x)/d), T2=T1, ωLT2 = Γ0T2 =10,  |
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| Fig.3: Current as a function of Θ, for ΓN/ΓF = 10, ωL/ΓF = 1, ΓF T1 = ΓF T1 = 10, and several values of p. | Fig.6: Magnetoresistance signal as a function of the perpendicular magnetic field **B** for several T2/T1, for p=0.8 and ΓF T1 = 10. The field **B**0 is parallel to the magnetization in the ferromagnet. |